

comparing the measured temperature to a target temperature;

heating the plasma processing chamber by heating a plurality of thermal control blocks that include at least a heater element and a cooling element arranged around the sides of the plasma processing chamber such that the thermal control blocks are thermally coupled to the plasma processing chamber; and

cooling the plasma processing chamber by actively cooling the plurality of thermal control blocks so that the cooling is provided by the cooling element through the heating element.

(Twice amended) 26. A method as recited in claim 23 [25], wherein the thermal control blocks further include a thermal break element coupled between the heater element and the cooling element.

(Amended) 32. A method as recited in claim 23, wherein the thermal control blocks further include notches configured to prevent RF energy from coupling with the thermal control blocks.

(Amended) 33. A method for providing temperature control to a plasma processing chamber of a plasma processing apparatus, said method comprising:

directly or indirectly measuring temperature internal to the plasma processing chamber;

comparing the measured temperature to a target temperature;

providing a thermal control block that is thermally coupled to the plasma processing chamber, said thermal control block having a heating element and a cooling element with a thermal break element coupled between the heater element and the cooling element;

heating the plasma processing chamber by heating the thermal control block that is thermally coupled to the plasma processing chamber; and

cooling the plasma processing chamber by actively cooling the thermal control block so that the cooling is provided by the cooling element through the heating element.

(Amended) 39. A method as recited in claim 38, wherein the [thermal control block
cooling] cooling of the plasma processing chamber is accomplished through the same thermal control block that is able to heat the plasma processing chamber, thereby providing more uniform temperature profile to the plasma processing chamber.

(Amended) 41. A method as recited in claim 40, wherein the thermal control block further includes a [-a] thermal break element coupled between the heater element and the cooling element.

Please **ADD** the following Claim:

-- 43. A method as recited in claim 23, wherein said biasing the thermal control blocks against a portion of the plasma processing chamber includes spring biasing the thermal control blocks against a portion of the plasma processing chamber. --

REMARKS

Again Applicant's representative thanks the Examiner for her guidance and courtesy in discussing this application on November 26, 2002. Claims 23, 26, 27, 32, 33, 35, 36, 39, and 41 have been amended (either directly or through dependence) herein and Claim 43 has been added. Claims 1-22, 24, 25, 28-31, and 34 now stand cancelled without prejudice. Therefore, Claims 23, 26, 27, 32, 33, and 35-43 are currently pending in this application. The applicants respectfully submit that this amendment places the claims in condition for allowance and also places the claims in better form for appeal. Accordingly, the applicants respectfully request entry of this amendment and request reconsideration of the remaining claims.

Rejections Under 35 U.S.C. § 103:

Claims 23-27 and 32-42 are rejected as being unpatentable over Collins, et al. EP0837489A2 (hereinafter *Collins*) under 35 U.S.C. § 103.